

METHOD FOR FORMING SACRIFICIAL OXIDE LAYER

ABSTRACT OF THE INVENTION

A method for forming a sacrificial oxide layer is disclosed. The invention utilizes an in situ steam generated process comprising the introductions of oxygen and hydroxyl to oxidize active regions of a substrate and form a sacrificial oxide layer. The ISSG process renders the sacrificial oxide layer much less stress and encroachment. Unlike the conventional sacrificial oxide layer, the sacrificial oxide layer formed by the method set forth will not damage the substrate. The electrical and mechanical properties of the active regions can be assured.